

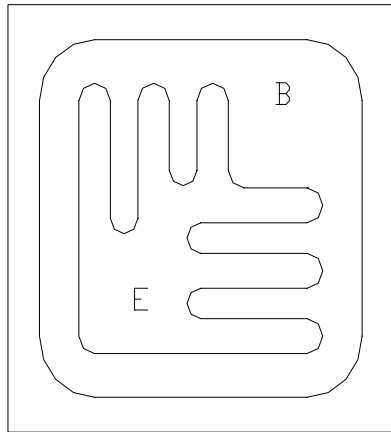
## BC817A Silicon NPN Epitaxial Transistor

Description: The BC817A is designed for audio frequency general amplifier applications

Features: ●Excellent  $h_{FE}$  Linearity

●Complementary to BC807A

## Chip Appearance

	Chip Size		440um × 440um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	110um × 110um
	Front Metal		Al
	Backside Metal		Au(As)
	Scribe line width		50um
	Wafer Size		6 inch

Electrical Characteristics(  $T_a=25^\circ\text{C}$  )

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=45\text{V}, I_E=0$		0.1	uA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=0.1\text{mA}$	50		V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=1\text{mA}$	45		V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=0.1\text{mA}$	5.0		V
DC Current Gain	$h_{FE}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	120	560	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.6	V